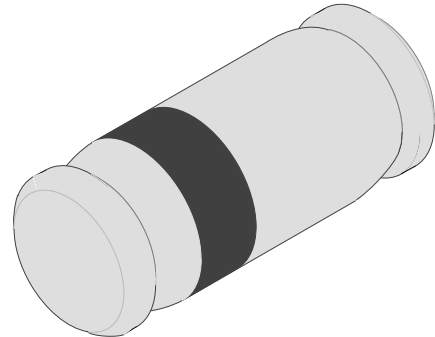


## Fast Switching Diode

### Features

- Silicon Epitaxial Planar Diodes
- Electrical data identical with the devices 1N4148 and 1N4448 respectively



94 9371

### Applications

Extreme fast switches

### Order Instruction

Type	Type Differentiation	Ordering Code	Remarks
LL4148	$V_{RRM} = 100 \text{ V}$ , $V_F@I_F 50\text{mA} = 1 \text{ V}$	LL4148 – GS08	Tape and Reel
LL4448	$V_{RRM} = 100 \text{ V}$ , $V_F@I_F 100\text{mA} = 1 \text{ V}$	LL4448 – GS08	Tape and Reel

### Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage			$V_{RRM}$	100	V
Reverse voltage			$V_R$	75	V
Peak forward surge current	$t_p=1\mu\text{s}$		$I_{FSM}$	2	A
Repetitive peak forward current			$I_{FRM}$	500	mA
Forward current			$I_F$	300	mA
Average forward current	$V_R=0$		$I_{FAV}$	150	mA
Power dissipation			$P_V$	500	mW
Junction temperature			$T_j$	175	$^\circ\text{C}$
Storage temperature range			$T_{stg}$	-65...+175	$^\circ\text{C}$

### Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mmx50mmx1.6mm	$R_{thJA}$	500	K/W

**Electrical Characteristics**

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=5\text{mA}$	LL4448	$V_F$	0.62		0.72	V
	$I_F=50\text{mA}$	LL4148	$V_F$		0.86	1	V
	$I_F=100\text{mA}$	LL4448	$V_F$		0.93	1	V
Reverse current	$V_R=20\text{V}$		$I_R$			25	nA
	$V_R=20\text{V}, T_j=150^\circ\text{C}$		$I_R$			50	$\mu\text{A}$
	$V_R=75\text{V}$		$I_R$			5	$\mu\text{A}$
Breakdown voltage	$I_R=100\mu\text{A}, t_p/T=0.01, t_p=0.3\text{ms}$		$V_{(BR)}$	100			V
Diode capacitance	$V_R=0, f=1\text{MHz}, V_{HF}=50\text{mV}$		$C_D$			4	pF
Rectification efficiency	$V_{HF}=2\text{V}, f=100\text{MHz}$		$\eta_r$	45			%
Reverse recovery time	$I_F=I_R=10\text{mA}, i_R=1\text{mA}$		$t_{rr}$			8	ns
	$I_F=10\text{mA}, V_R=6\text{V}, i_R=0.1I_R, R_L=100\Omega$		$t_{rr}$			4	ns

**Characteristics ( $T_j = 25^\circ\text{C}$  unless otherwise specified)**

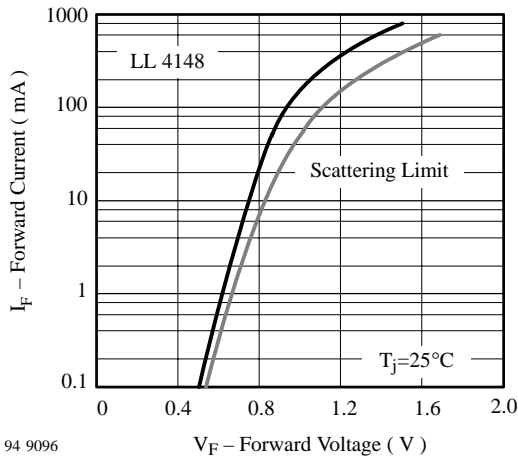


Figure 1. Forward Current vs. Forward Voltage

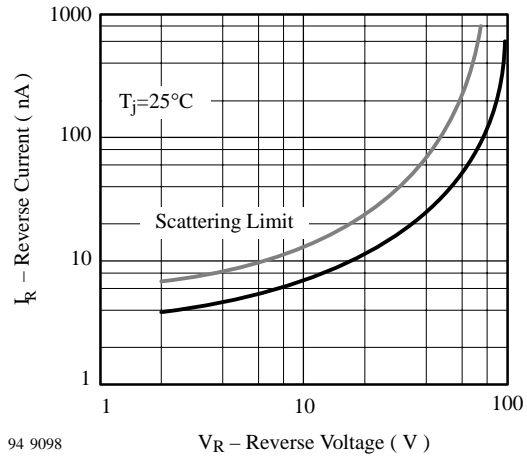


Figure 3. Reverse Current vs. Reverse Voltage

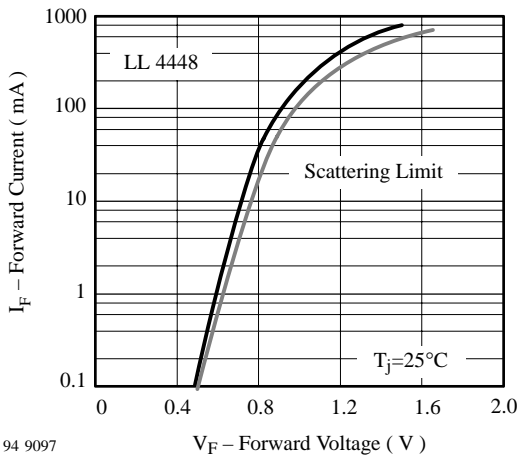


Figure 2. Forward Current vs. Forward Voltage

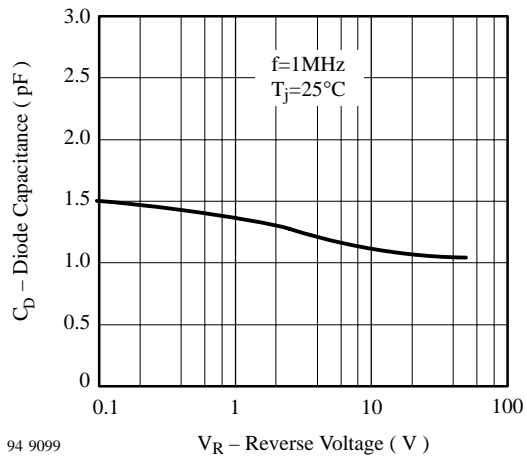
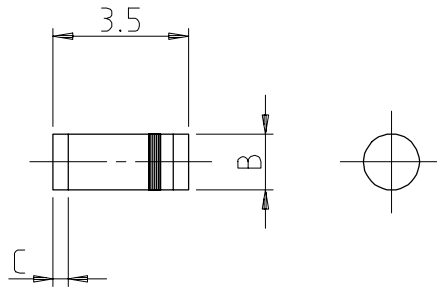


Figure 4. Diode Capacitance vs. Reverse Voltage

**Dimensions in mm**


MiniMELF		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50
All Dimensions in mm		

15833

